



**THE DATASHEET OF
NIS5102QP1HT1G**



NIS5102

High Side SMART HotPlug™ IC/Inrush Limiter/Circuit Breaker

The NIS5102 is a controller/FET IC that saves design time and reduces the number of components required for a complete hot swap application. It is designed for +12 V applications.

This chip includes a time delay for sequencing applications. It has a dual function OVLO pin that allows multiple units to be ganged together for simultaneous turn-on and shutdown, allowing units to be operated in parallel. It allows for user selectable undervoltage and overvoltage lockout levels. Its unique current limit circuit allows for adjustable current limit levels with no external power resistor. An internal temperature limiting circuit greatly increases the reliability of this device.

Features

- Integrated Power Device
- Power Device Thermally Protected
- No External Current Shunt Required
- Simultaneous Shutdown and Startup for Parallel Operation
- Enable/Timer Pin
- Power Good
- 9.0 to 18 V Input Range
- 10 mΩ
- Main/Mirror MOSFET Current Ratio 1000:1
- Pb-Free Packages are Available

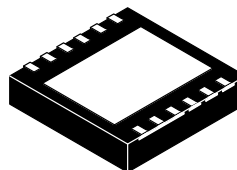
Typical Applications

- High Availability Systems
- Electronic Circuit Breaker
- 12 V Distributed Architecture



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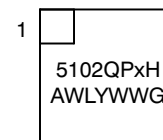
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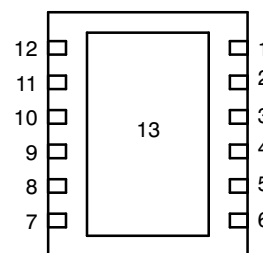
12 PIN PLLP, 9x9 mm
CASE 488AB

- x = 1 or 2
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free

MARKING DIAGRAM



PIN CONNECTIONS



(Bottom View)

ORDERING INFORMATION

Device	Package	Shipping†
NIS5102QP1HT1 (Latchoff)	9x9 mm 12 Pin PLLP	1500/Tape & Reel
NIS5102QP1HT1G (Latchoff)	12 Pin PLLP (Pb-Free)	1500/Tape & Reel
NIS5102QP2HT1 (Auto-Retry)	9x9 mm 12 Pin PLLP	1500/Tape & Reel
NIS5102QP2HT1G (Auto-Retry)	12 Pin PLLP (Pb-Free)	1500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NIS5102

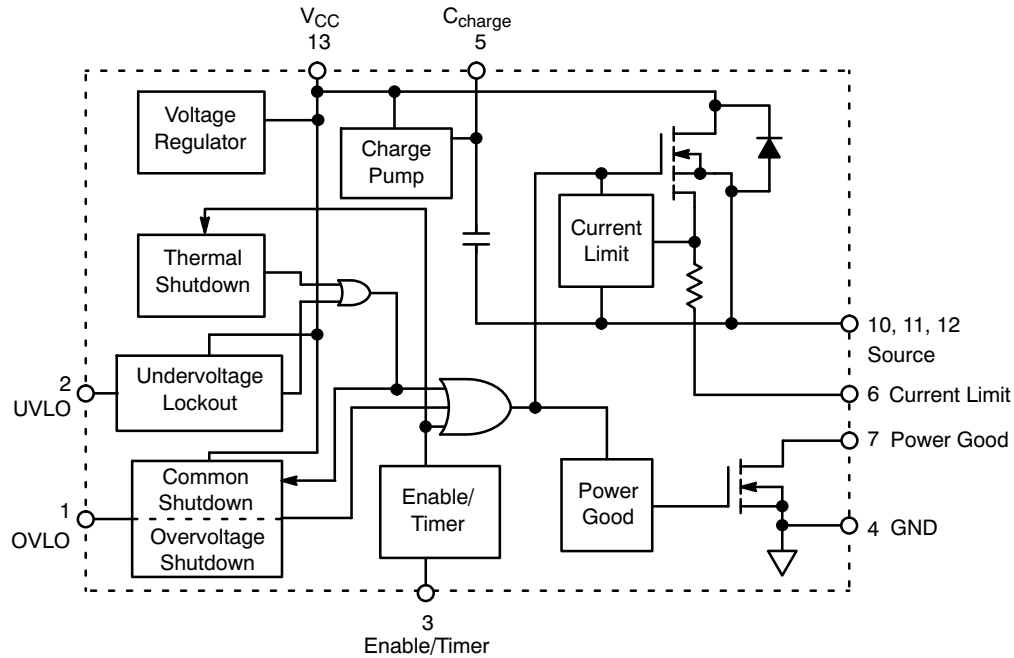


Figure 1. Block Diagram

PIN FUNCTION DESCRIPTION

Pin	Function	Description
1	OVLO	The overvoltage shutdown point is programmed by a resistor from this pin to the V_{CC} supply. When tied together with other devices, this pin also communicates a shutdown state due to undervoltage and overtemperature reasons. All devices connected will simultaneously shutdown. Startup for this condition may be simultaneous or sequenced.
2	UVLO	A resistor from V_{CC} to the UVLO pin adjusts the voltage at which the device will turn on.
3	Enable/Timer	A high level signal on this pin allows the device to begin operation. Connection of a capacitor will delay turn on for timing purposes. A low input signal inhibits the operation, and communicates to any other paralleled devices (via the OVLO pin) to shutdown. This signal can also be used to reset the thermal latch.
4	Ground	Negative input voltage to the device. This is used as the internal reference for the IC.
5	C_{charge}	An external capacitor is required from this pin to the source pin. This is the storage capacitor for the internal charge pump. A small internal capacitor is included for noise filtering.
6	I_{LIMIT}	A resistor (R_{LIMIT}) tied from this pin to the source pin sets the current limit level.
7	Power Good	A high impedance signal on this pin indicates that the power device is conducting.
8, 9	No Connection	-
10, 11, 12	Source	Source of power FET, which is also the switching node for the load.
13	V_{CC}	Positive input voltage to the device.

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Input Voltage, Operating, Steady-State (Input + to Input -)	V_{in}	-0.3 to 18	V
Input Voltage, Operating, Transient (Input + to Input -), 1 second	V_{in}	-0.3 to 25	V
Drain Voltage, Operating, Steady-State (Drain to Input -)	V_{DD}	-0.3 to 18	V
Drain Voltage, Operating, Transient (Drain to Input -), 1 second	V_{DD}	-0.3 to 25	V
Drain Current, Peak	I_{Dpk}	20	A
Continuous Current ($T_A = 25^\circ\text{C}$, 0.5 in ² pad)	I_{Davg}	10	A
Voltage on Power Good Pin (Pin 7)	V_{max7}	20	V
Thermal Resistance, Junction-to-Air 0.5 in ² Copper 1 in ² Copper	Q_{JA}	76.5 41.2	$^\circ\text{C/W}$ $^\circ\text{C/W}$
Thermal Resistance, Junction-to-Lead	Q_{JL}	3.2	$^\circ\text{C/W}$
Power Dissipation ($T_A = 25^\circ\text{C}$, 0.5 in ² pad)	P_{max}	1.4	W
Operating Temperature Range (Note 1)	T_J	-40 to 175	$^\circ\text{C}$
Non-Operating Temperature Range	T_J	-55 to 175	$^\circ\text{C}$
Lead Temperature, Soldering (10 Sec)	T_L	235	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Actual maximum junction temperature is limited by an internal protection circuit and will not reach the absolute maximum temperature as specified.

ELECTRICAL CHARACTERISTICS ($V_{CC} = 12\text{ V}$, $R_{LIMIT} = 36\ \Omega$, $C_{Charge} = 100\text{ pF}$, $T_J = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
POWER FET					
Delay Time (Enable High to $I_S = 100\text{ mA}$)	T_{dly}	-	2.0	-	ms
Charging Time ($I_S = 100\text{ mA}$ to $I_S = 5.0\text{ A}$, $R_{LIMIT} = 36\ \Omega$)	t_{chg}	-	1.0	-	ms
ON Resistance ($V_{CC} = 12\text{ V}$, $I_S = 5.0\text{ A}$) (Note 2)	R_{DSon}	-	10	13	m Ω
Zero Gate Voltage Drain Current ($V_{DS} = 12\text{ V}_{dc}$, $V_{GS} = 0\text{ V}_{dc}$)	I_{DSS1}	-	-	10	μA
Zero Gate Voltage Drain Current ($V_{DS} = 18\text{ V}_{dc}$, $V_{GS} = 0\text{ V}_{dc}$)	I_{DSS2}	-	-	100	μA
Output Capacitance ($V_{DS} = 12\text{ V}_{dc}$, $V_{GS} = 0\text{ V}_{dc}$, $f = 10\text{ kHz}$)	-	-	-	-	pF

THERMAL LIMIT

Shutdown Temperature (Note 3)	T_{SD}	125	135	145	$^\circ\text{C}$
Hysteresis (Note 3)	T_{hyst}	-	40	-	$^\circ\text{C}$

OVER/UNDERVOLTAGE

UVLO Turn-on (Input + Increasing, $R_{extUVLO} = 620\text{ k}$)	V_{on}	10.05	11.15	12.30	V
UVLO Hysteresis (Input + Decreasing, $R_{extUVLO} = 620\text{ k}$)	V_{hyst}	0.45	0.62	0.75	V
OVLO Turn-off (Input + Increasing, $R_{extUVLO} = 620\text{ k}$)	V_{off}	14.0	16.4	19.0	V
OVLO Hysteresis (Input + Decreasing, $R_{extUVLO} = 620\text{ k}$)	V_{hyst}	0.6	0.78	1.0	V

PARALLEL SHUTDOWN (Alternate Function on OVLO Pin)

Device Fan-out (Minimum External Resistor Value = 2.0 k Ω) (Note 3)	N_{fan}	-	-	4.0	Devices
Shutdown Voltage Threshold (OVLO Pin)	V_{SD}	0.6	0.8	-	V
Shutdown State Output Voltage ($I_{sink} = 2.0\text{ mA}$)	V_{low}	-	0.3	0.4	V

- Pulse Test: Pulse width 300 μs , duty cycle 2%.
- Verified by design.

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ELECTRICAL CHARACTERISTICS (continued) ($V_{CC} = 12\text{ V}$, $R_{LIMIT} = 36\ \Omega$, $C_{Charge} = 100\text{ pF}$, $T_J = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
CURRENT LIMIT					
Current Limit (Short Circuit, $R_{LIMIT} = 36\ \Omega$)	I_{LIM1}	3.8	4.8	5.8	A
Current Limit (Overload, $R_{LIMIT} = 36\ \Omega$) (Note 3)	I_{LIM2}	7.0	7.8	8.6	A
ENABLE/TIMER					
Enable Voltage (Turn-On)	V_{ENon}	2.2	-	-	V
Enable Voltage (Turn-Off)	V_{ENoff}	-	-	1.6	V
Charging Current (Into External Capacitor)	I_{Charge}	65	77	88	μA
Turn-on Delay (Time from Enable High to $I_{source} = 100\text{ mA}$)	t_{delay}	-	2.2	-	ms
CHARGE PUMP					
C_{Charge} (Voltage on Pin 5 with Respect to Ground) $V_{CC} = 18\text{ Vdc}$	$V_{Ccharge}$	-	18	-	V
		-	26	-	V
POWER GOOD					
Power Good \rightarrow High Z Signal when FET is Fully Enhanced	-	-	-	-	-
Low Z State Output Voltage ($I_{Sink} = 2\text{ mA}$)	V_{pin7}	-	230	300	mV
Leakage Current ($V_{pin7} = 12\text{ V}$, High Z State)	I_{Leak}	-	2.0	10	μA
Power Good Delay (Time from Power FET is Fully Enhanced to Power Good FET Changing State)	$t_{pwrgood}$	-	15	-	ms
TOTAL DEVICE					
Bias Current (Operational, $V_{CC} = 12\text{ V}$)	I_{Bias}	-	1.3	2.0	mA
Bias Current (Non-operational, $V_{CC} = 7\text{ V}$)	I_{Bias}	-	400	700	μA
Minimum Operating Voltage	V_{CCmin}	-	8.5	9.0	V

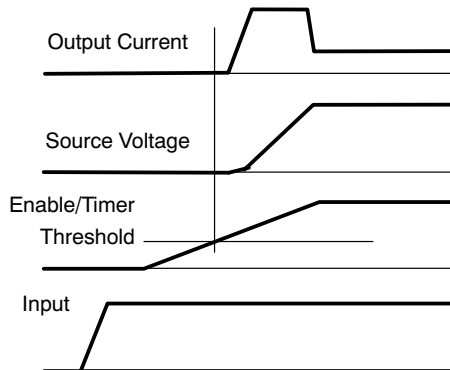


Figure 2. Timing Diagram for External Enabled Delay

TYPICAL PERFORMANCE CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

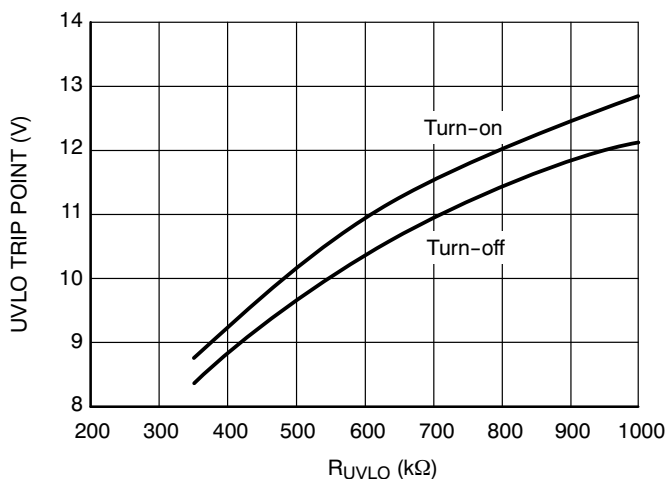


Figure 3. UVLO Adjustment

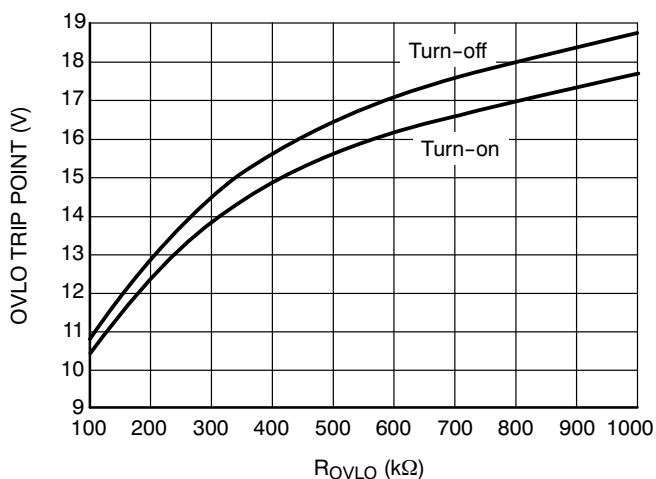


Figure 4. OVLO Adjustment

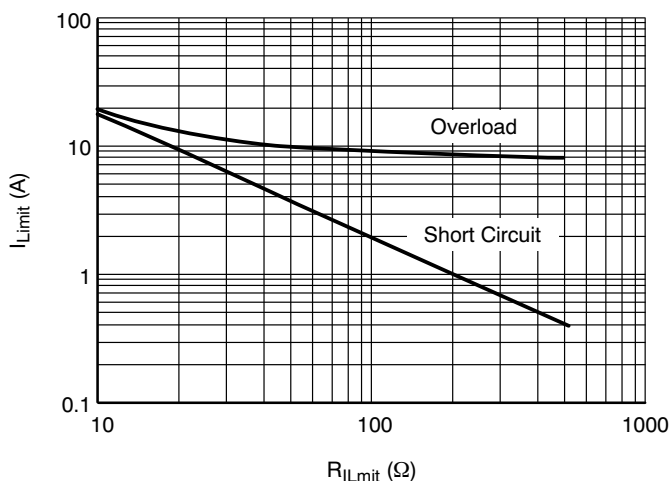


Figure 5. Current Limit Adjustment

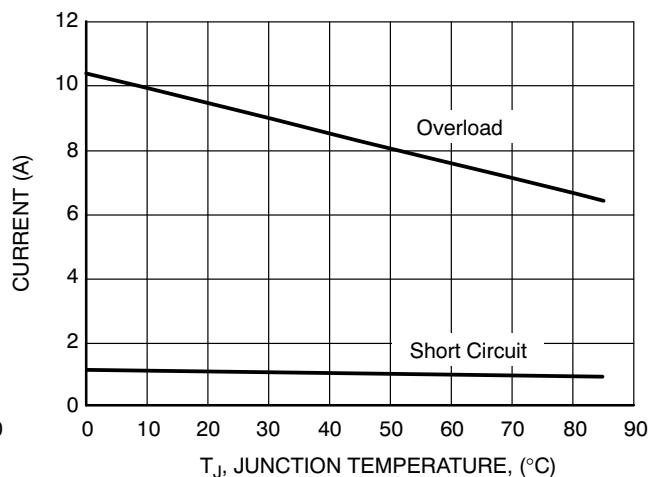


Figure 6. Current Limit vs. Temperature for 182Ω

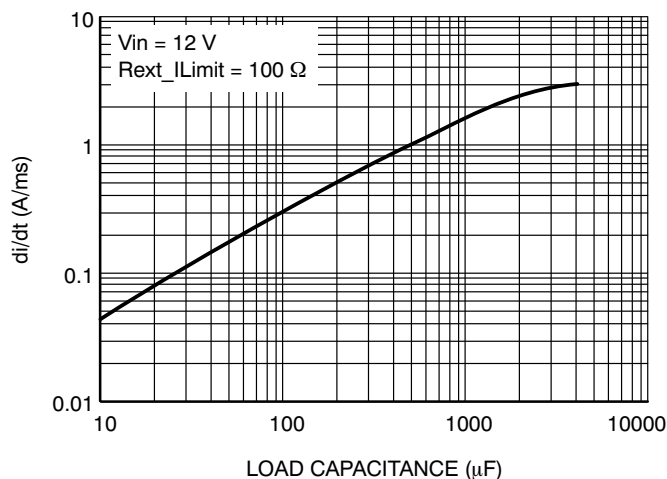


Figure 7. Load Capacitance vs. Output di/dt

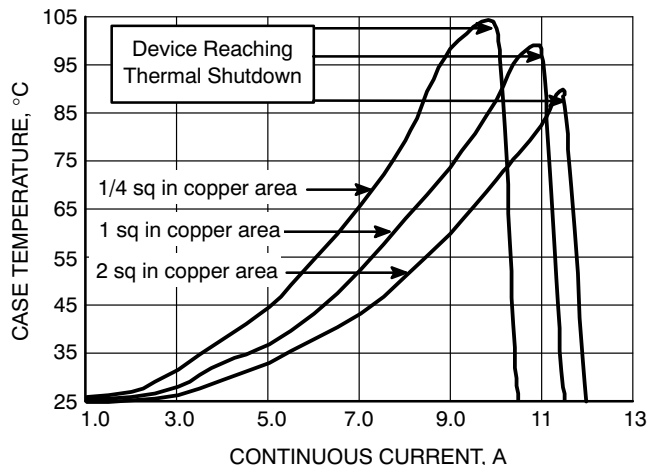


Figure 8. Continuous Current vs. Case Temperature (Test performed on a double-sided copper board, 1 oz)

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TYPICAL PERFORMANCE CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

UVLO Trip Point, Volts

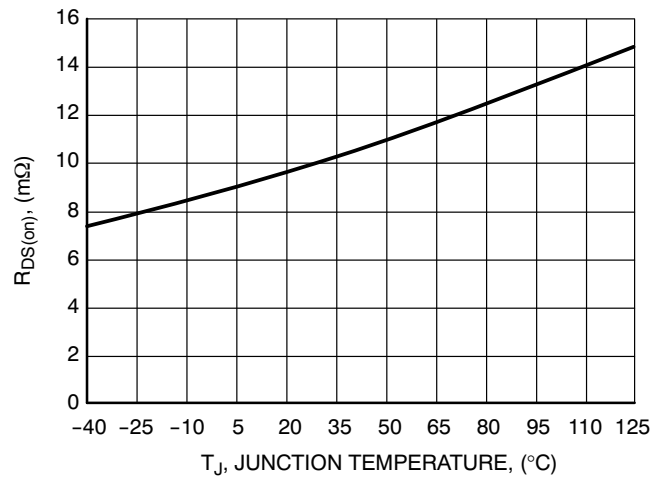


Figure 9. Typical $R_{DS(on)}$ vs. Junction Temperature

TYPICAL APPLICATION CIRCUITS AND OPERATION WAVEFORMS

($T_A = 25^\circ\text{C}$ unless otherwise noted)

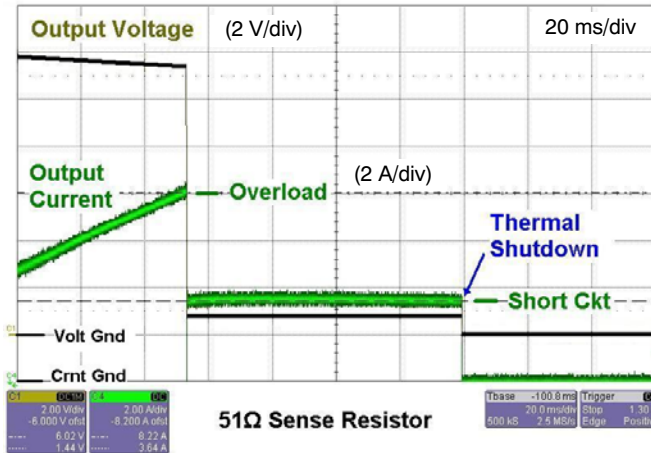


Figure 10. Current Waveforms for Overload, Short Circuit and Thermal Shutdown

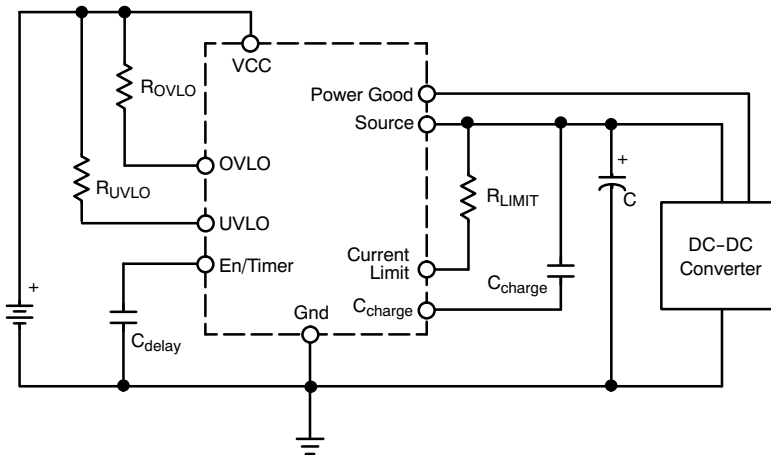


Figure 11. Typical Applications Circuit

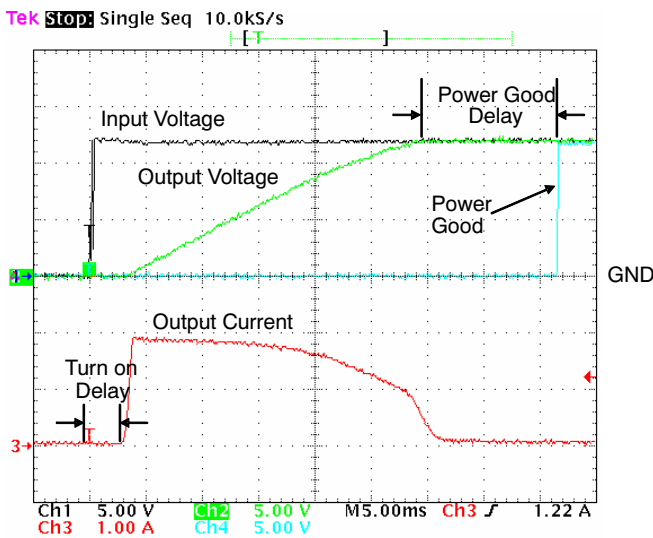


Figure 12. Turn-on Waveforms for 3300 μF Load Capacitors

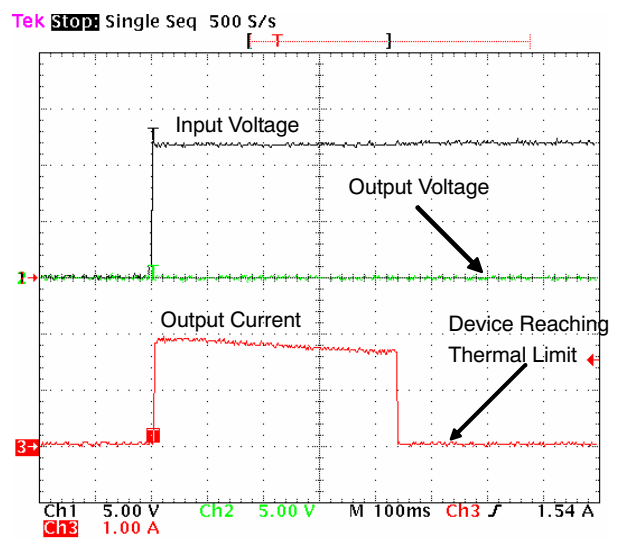


Figure 13. Turn-on Waveforms for Shorted Output, Latchoff Device

TYPICAL APPLICATION CIRCUITS AND OPERATION WAVEFORMS (continued)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

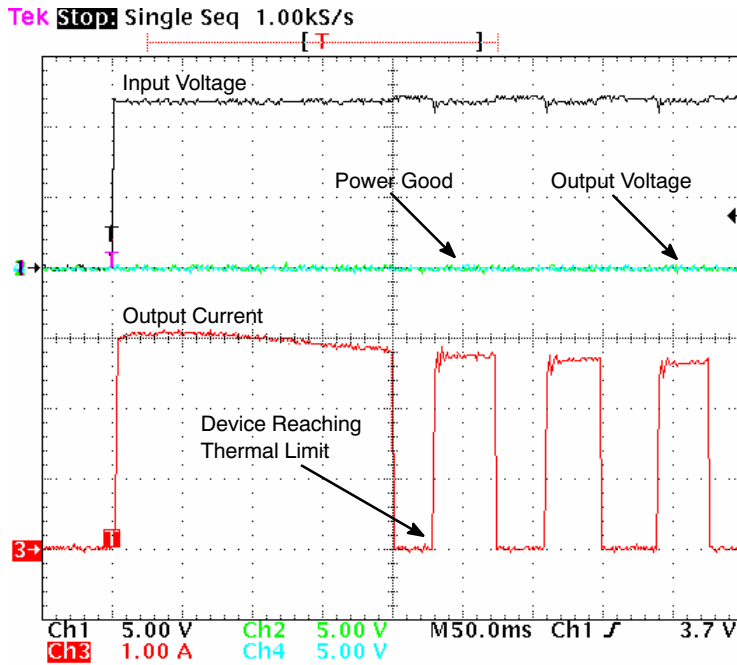


Figure 14. Turn-On Waveforms for Shorted Output, Auto-Retry Device

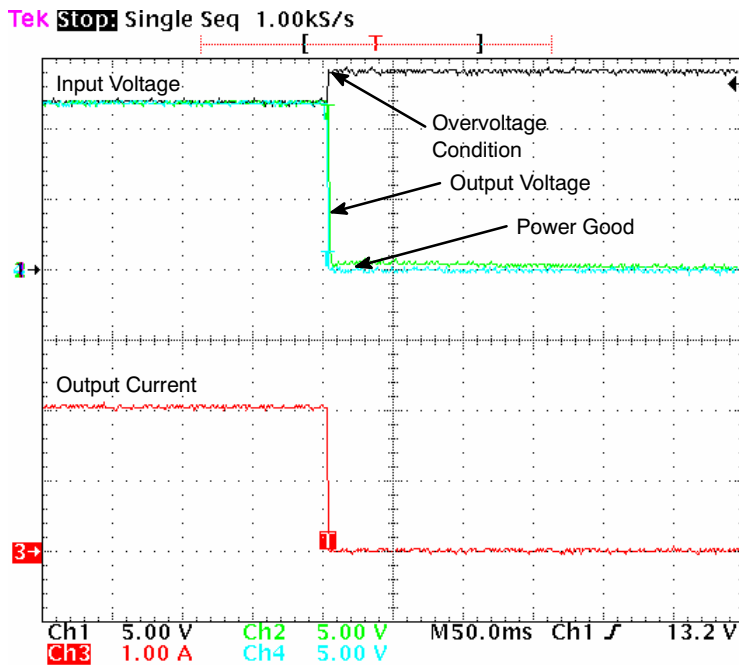


Figure 15. Device Response During an Overvoltage Condition

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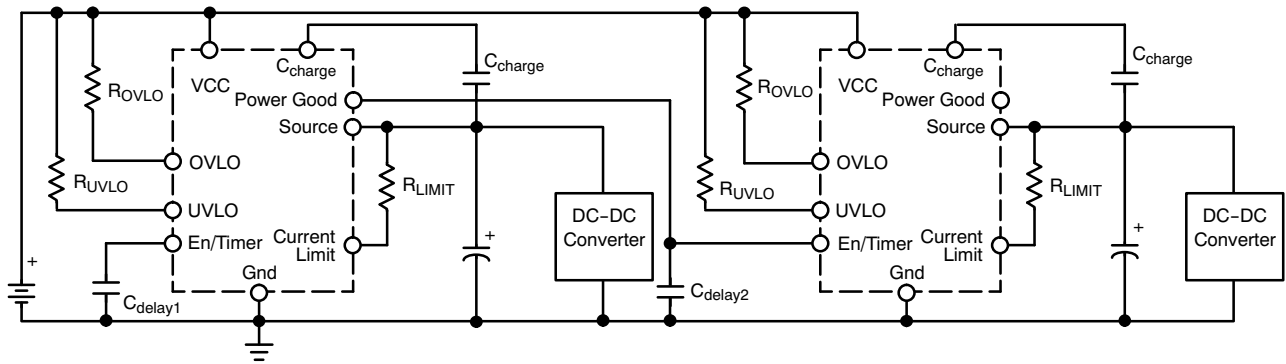


Figure 16. Turn-on Sequencing Using Power Good Signal

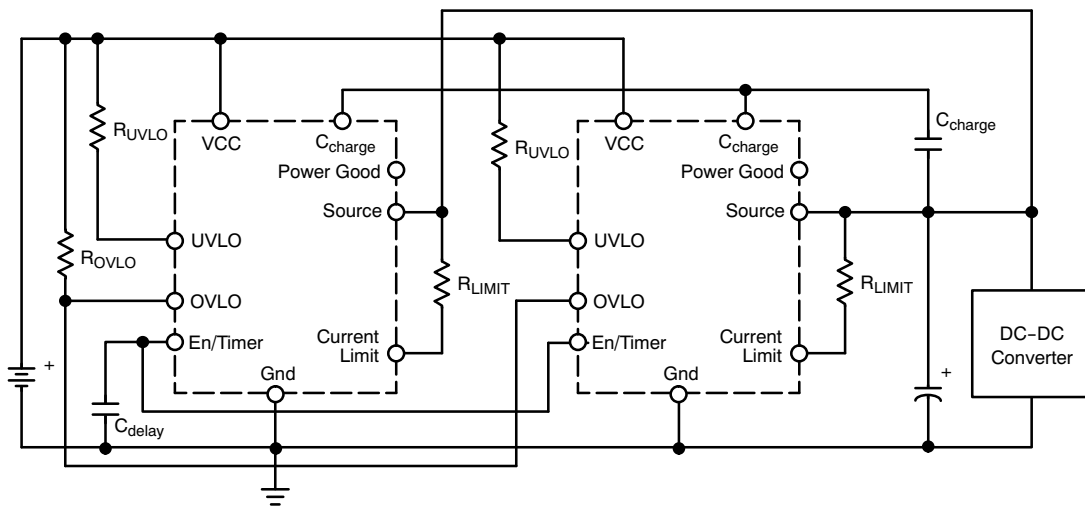


Figure 17. Parallel Operation / Simultaneous Turn-on and Shutdown

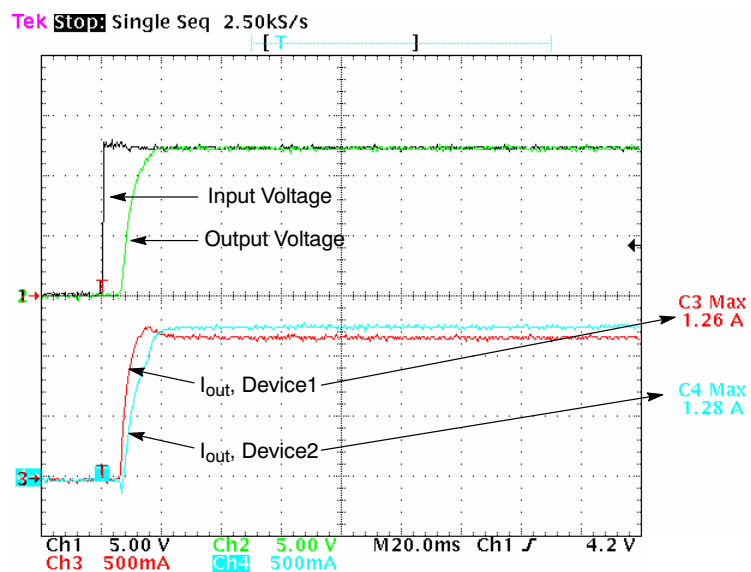


Figure 18. Turn-on Waveforms for Parallel Operation

OPERATING DESCRIPTION

Operation

The NIS5102 has a variety of shutdown and protection features that make this part extremely versatile as well as rugged. For the unit to operate, the input voltage must be within the operating range of the part which is set by the UVLO and OVLO bias resistors. The enable must also be high for operation. Current and thermal limit circuits constantly monitor the operation and will protect the unit if either of these parameters exceeds its preset limit.

An additional shutdown method, is the use of the OVLO pin, which can be tied in parallel. This allows multiple units to be either operated in parallel, and will shutdown and turn on simultaneously for any fault other than an overvoltage, or it allows these hot plug devices to control independent loads, and shutdown and turn on simultaneously.

Faults

Once the load capacitance is charged, the SENSEFET™ will become fully enhanced as long as the current does not

reach the current limit threshold, or is shutdown due to an overvoltage, undervoltage or thermal fault. Both the UVLO and OVLO circuits incorporate hysteresis to assure clean turn-on and turn-offs with no chatter. The thermal latching circuit will require the input power to be recycled to resume operation after a fault. The current limit is always active, so any transient or overload will always be limited.

Circuit Description

Enable/Timer

The enable/timer pin can function either as a direct enable pin, or as a time delay. In the enable mode, an open collector device is connected to this pin. When the device is in its low impedance mode, this pin is low and the operation of the chip is disabled. If a time delay is required, a capacitor is added to this pin. Figure 19 shows the equivalent circuit for the enable.

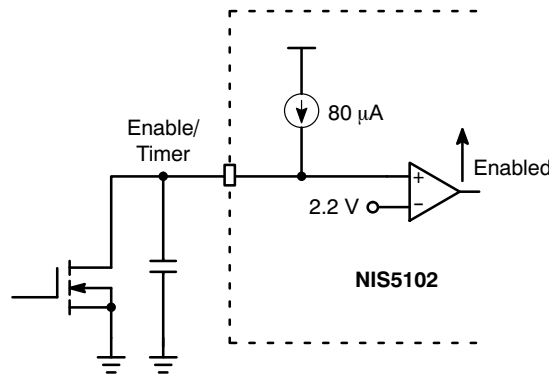


Figure 19. Enable/Timer Circuit

If a capacitor is added without an open collector device, the turn on will be delayed from the time at which the UVLO voltage is reached. If an open collector device is also used, the delay will start from the time that it goes into its high impedance state. The capacitor is charged by an internal current source.

There is an inherent delay in the turn on of the hot plug device, due to the method of gate drive used. The gate of the power FET is charged through a high impedance resistor, and from the time that the gate starts charging until the time that it reaches its threshold voltage, there will be no conduction. Once the gate reaches its threshold voltage, the output current will begin a controlled ramp up phase.

This delay will be added to any timing delay due to the enable/timer circuit.

Power Good

The power good circuit monitors the V_{GS} voltage of the power SENSEFET and compares it with the output voltage

of the internal charge pump. Once the V_{GS} of the power SENSEFET reaches around 90% of the internal charge pump output voltage, the power good will change its state from low impedance to high impedance but only after the power good delay has elapsed. Figure 12 shows the power good behavior during the startup of the NIS5102 device, an external pullup resistor from power good to V_{CC} was used.

The power good will change its state from high impedance to low impedance in the event of any fault condition such as short circuit and overvoltage.

Undervoltage Lockout

The UVLO circuit holds the chip off when the input voltage is less than the turn-on limit. It includes internal hysteresis to assure clean on/off switching. An internal divider sets the turn-on voltage level at 16 V. This voltage can be reduced by adding an external resistor from the UVLO pin to the V_{CC} pin. The equivalent circuit is shown in Figure 20.

For this equation, V_{ref} is the reference voltage of the current limit circuit, and R_{DSon} is the on resistance of the SENSEFET. For more information on this, see application note AND8140/D, “SMART HotPlug™ Current Limit Function”.

This inherent property of the SENSEFET allows for simple dual level current limiting, in which a short circuit condition will see a lower level of limiting than will an overload. This operation will exist in start up as well as under normal operation, so the device will be able to differentiate between a short and an overload.

As with all SMART HotPlug devices, the current limit will never shutdown the device. Only the thermal limit will stop the flow of current to the load. Once the current is stopped due to the thermal limit, it will remain off until input power is recycled for the latching version, or it will continuously retry to start again if it is the auto-retry version.

The I_{Limit} graph shown in Figure 5 was generated from the data of the I_{Limit} characterization, the formula for the short circuit curve is:

$$R_{ILimit} (\Omega) = \left(\frac{152.86}{I_{Limit}} \right)^{1.02} \text{ for } T_J = 25^\circ\text{C}$$

where “ I_{Limit} ” is the desired short circuit I_{Limit} value, and R_{ILimit} is the programming resistor from the I_{Limit} pin to the source pin.

Turn-on Surge

During the turn-on event, there is a large amount of energy dissipated due to the linear operation of the power device. The energy rating is the amount of energy that the device can absorb before the thermal limit circuit will shut the unit down. This is very important specially for the latch off device as it determines the maximum load capacitance that the device can charge before the thermal limit shuts the device down. The calculation of this is not very simple as it depends on several factors such as the input voltage (V_{in}), load capacitance (CL), current limit settings (I_{Limit}) and device’s thermal transient response, therefore, it is recommended to do lab evaluations for these purposes. Figure 22 shows the device’s thermal transient response for minimum pad.

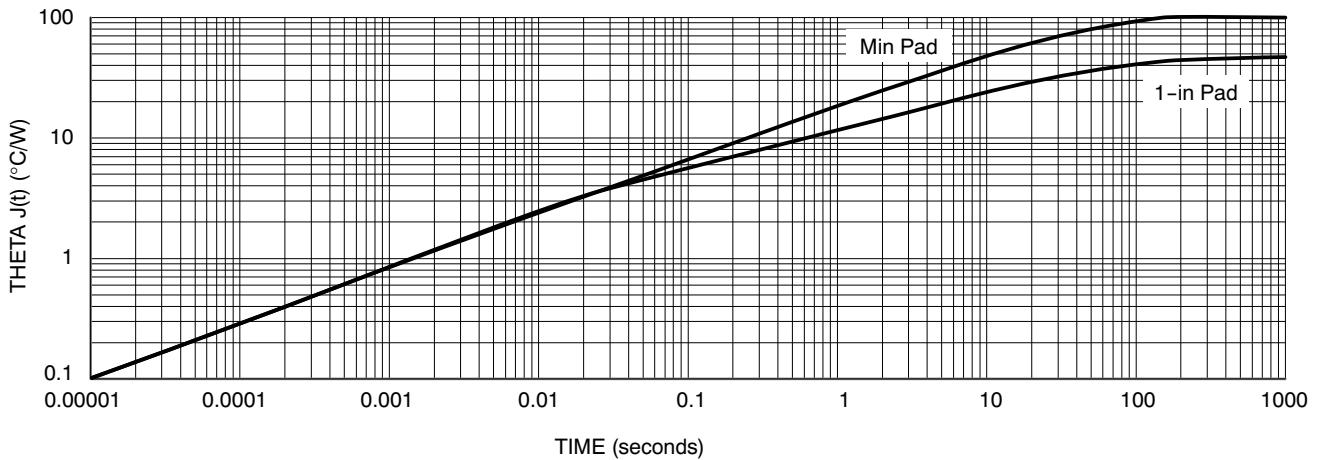
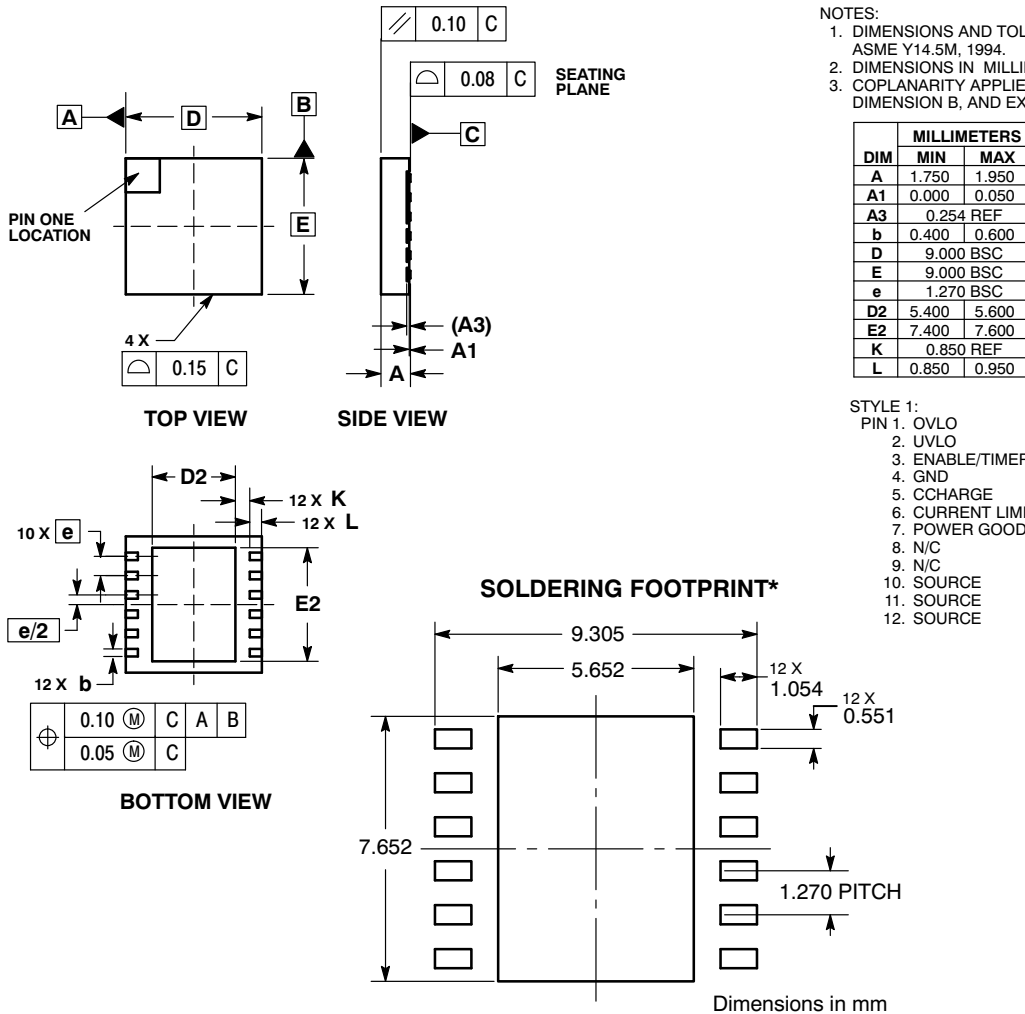


Figure 22. Thermal Transient Response

NIS5102

PACKAGE DIMENSIONS

PLL_P-12, 9x9 mm
CASE 488AB-01
ISSUE C



- NOTES:
1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
 2. DIMENSIONS IN MILLIMETERS.
 3. COPLANARITY APPLIES TO THE LEAD, DIMENSION B, AND EXPOSED PAD.

STYLE 1:

1. OVLO
2. UVLO
3. ENABLE/TIMER
4. GND
5. CHARGE
6. CURRENT LIMIT
7. POWER GOOD
8. N/C
9. N/C
10. SOURCE
11. SOURCE
12. SOURCE

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

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